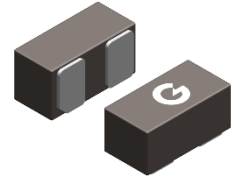
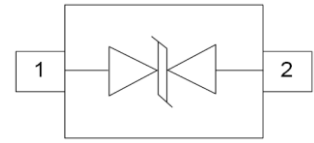


Features

- ESD / transient protection of high speed data lines
 - IEC 61000-4-2 (ESD): $\pm 20\text{ kV}$ (air), $\pm 15\text{ kV}$ (contact)
- Low reverse stand-off voltage: 3.3 V
- Very low leakage current
- Low diode capacitance
- ESD protection up to 10 kV ; IEC61000-4-2

HF



DFN0603-2L

Mechanical Data

- Case: DFN0603-2L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin-Plated Leads, Solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
GESD3V3X1BLP3	DFN0603-2L	10000 pcs / Tape & Reel	3XB

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
IEC 61000-4-2; ESD (Air) ^{*1}	$V_{\text{ESD-A}}$	± 20	kV
IEC 61000-4-2; ESD (Contact) ^{*1}	$V_{\text{ESD-C}}$	± 15	kV
JESD22-A114-B; ESD (Human Body) ^{*1}	$V_{\text{ESD-HB}}$	± 10	kV
JESD22-A114-B; ESD (Machine) ^{*1}	$V_{\text{ESD-M}}$	± 0.4	kV
Peak Pulse Power ($t_p = 8/20\mu\text{s}$) ^{*2}	P_{PP}	68	W
Peak Pulse Current ($t_p = 8/20\mu\text{s}$) ^{*2}	I_{PP}	4	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Junction Temperature	T_J	$-55 \sim +125$	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Stand-off Voltage	V_{RWM}		-	-	3.3	V
Reverse Breakdown Voltage	$V_{(BR)}$	$I_T = 1\text{mA}$	4.2	-	-	V
Reverse Leakage Current	I_R	$V_{RWM} = 3.3\text{V}$	-	-	1	μA
Clamping Voltage *2	V_C	$I_{PP} = 1\text{A}$, $t_p = 8/20\mu\text{s}$	-	-	12	V
Clamping Voltage *2	V_C	$I_{PP} = 4\text{A}$, $t_p = 8/20\mu\text{s}$	-	-	17	V
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$	-	0.4	0.9	pF

Notes:

1. Device stressed with ten non-repetitive ESD pulses, measured from pin 1 to pin 2
2. Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5

Ratings and Characteristic Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

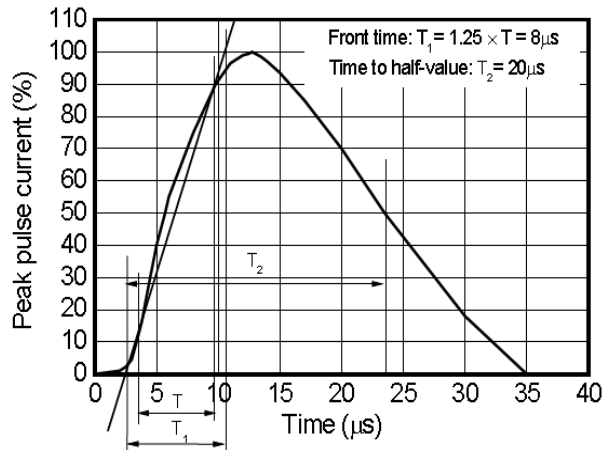


Fig 1 8/20 μs waveform per IEC61000-4-5

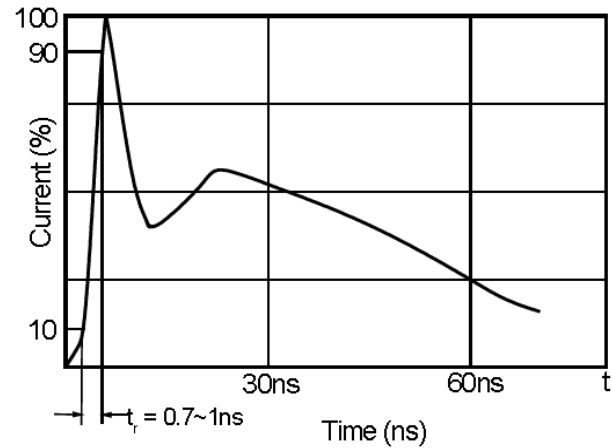


Fig 2 ESD pulse waveform according to IEC61000-4-2

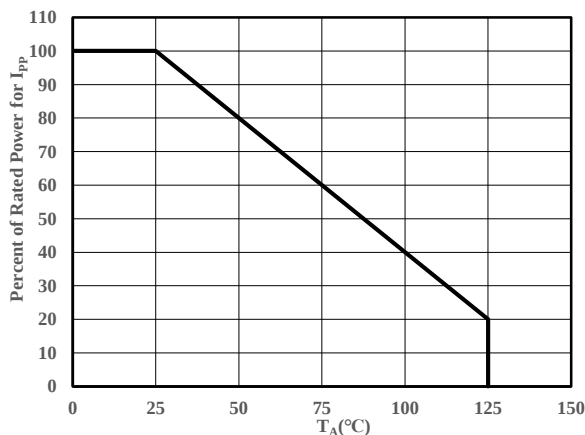
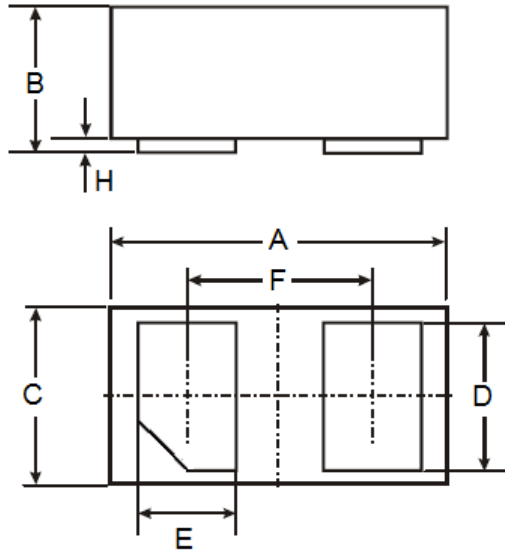


Fig 3 Power Derating Curve

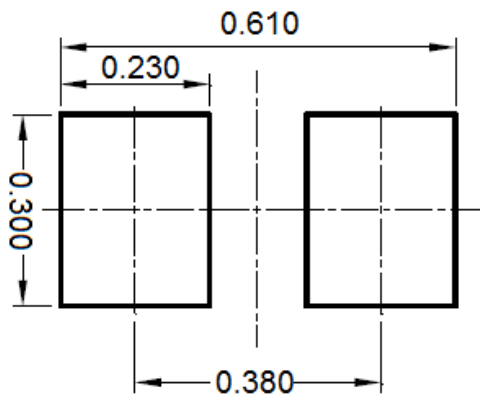
Package Outline Dimensions (Unit: mm)



DFN0603-2L			
Dimension	Min.	Typ.	Max.
A	0.595	0.620	0.645
B	0.270	0.300	0.350
C	0.295	0.320	0.345
D	0.190	0.240	0.290
E	0.140	0.190	0.240
F	-	0.355	-
H	0	0.020	0.030

Mounting Pad Layout (Unit: mm)

DFN0603-2L



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